2SB1375 TRANSISTOR (PNP)

1.BASE
2.COLLECTOR
3.EMITTER

TO-220C

FEATURES

- High Power Dissipation: P_C=25W(T_C=25℃)
- Low voltage:V_{CE}(sat)=-1.5V(Max)(I_C=-2A,I_B=-0.2A)
- Collector Metal(Fin)is Coverd with Mold Regin
- Complementary to 2SD2012

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Dissipation	2	W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-50mA,I_B=0	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	-7			V
Collector cut-off current	I_{CBO}	V_{CB}=-60V,I_E=0			-10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-7V,I_C=0			-10	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-5V,I_C=-0.5A	100		320	
	$h_{FE(2)}$	V_{CE}=-5V,I_C=-2A	15			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-2A,I_B=-0.2A			-1.5	V
Base-emitter voltage	V_{BE}	V_{CE}=-5V,I_C=-0.5A			-1	V
Transition frequency	f_T	V_{CE}=-5V,I_C=-0.5A		9		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		50		pF